

AMENDMENTS

IN THE CLAIMS

10. (Currently Amended) A space transformer comprising:

a silicon medium; and

a predetermined contact pattern comprising electrically conductive material disposed in an inner region of the substrate and defining electrical contact zones located to provide double-sided electrical contacts for the space transformer, the contacts comprising land grid array side contacts ~~having dimensions and spacing in the order of mils~~, and semiconductor side contacts ~~having dimensions and spacing in the order of microns~~, said land grid array side contacts having dimensions and spacing less than said semiconductor side contacts.

11. (Original) The space transformer according to claim 10, wherein the silicon medium comprises a first silicon layer and a second silicon layer, the contact pattern being disposed between the first silicon layer and the second silicon layer.

12. (Previously amended) The space transformer according to claim 11, wherein the second silicon layer defines at least one via therein, at least some of the electrically conductive material being located in the at least one via.

13. (Original) The space transformer according to claim 11, further comprising an adhesion promoter disposed between the electrically conductive material and the first silicon layer.

14. (Currently Amended) A space transformer comprising:

a first silicon layer defining a plurality of vias therein;

a predetermined contact pattern comprising copper on the first silicon layer, at least some of the copper being disposed in the plurality of vias for defining electrical contact zones in the plurality of vias to provide double-sided electrical contacts for the space transformer, ~~the contacts comprising land grid array side contacts having dimensions and spacing in the order of mils, and semiconductor side contacts having dimensions and spacing in the order of microns; and~~

a second silicon layer disposed on the contact pattern, the contact pattern being disposed in an inner region located between the first silicon layer and the second silicon layer, the contacts comprising land grid array side contacts and semiconductor side contacts, said land grid array side contacts having dimensions and spacing less than said semiconductor side contacts.

15. (Original) The space transformer according to claim 14, further comprising a layer of adhesion promoter disposed between the electrically conductive material and the first silicon layer.

16. (Currently Amended) A space transformer comprising:

a first silicon layer;

a second silicon layer mounted to the first silicon layer; and

means disposed in an inner region located between the first silicon layer and the second silicon layer for providing double-sided electrical contacts for the space transformer, the contacts comprising land grid array side contacts ~~having dimensions and spacing in the order of mils,~~ and semiconductor side contacts ~~having dimensions and spacing in the order of microns,~~ said land grid array side contacts having dimensions and spacing less than said semiconductor side contacts.

17. (Original) The space transformer according to claim 16, wherein the means for providing comprises a contact pattern comprising electrically conductive material.